

NVHL070N120M3S

Silicon Carbide (SiC) MOSFET – EliteSiC, 65 mohm, 1200 V, M3S, TO-247-3L

Product Overview

For complete documentation, see the data sheet.

The new family of 1200V M3S planar SiC MOSFETs is optimized for fast switching applications. Planar technology works reliably with negative gate voltage drive and turn off spikes on the gate. This family has optimum performance when driven with 18V gate drive but also works well with 15V gate drive.

Features

- Typical RDS(on) = 65m at Vgs =18V, Id = 15A
- Qualified for Automotive According to AECQ101
- New M3S technology: 65mohm RDS(ON) with low EON and EOFF losses
- Devices are PbFree and are RoHS Compliant
- 15V to 18V Gate Drive

Applications

- On Board Charger (OBC)
- DC/DC converters for EV/HEV

End Products

- Automotive EV/HEV

Part Electrical Specifications

Product	Status	Compliance	Family	Blocking Voltage BV _{DS} s (V)	I _{D(max)} (A)	R _{D(on)} Typ @ 25°C (mΩ)	Q _g Total (nC)	Output Capacitance (pF)	T _j Max (°C)	Package Type	Case Outline	MSL Type	MSL Temp (°C)	Container Type	Container Qty.
NVHL070N120M3S	Active, New		M3S	1200	34	65	57	57	175	TO-247-3LD	340 CX-PDF	NA	0	TUBE	450